

A cross-sectional view of a semiconductor device 70. The device features a substrate 72 with a patterned layer 73 on top. A central region 76 contains a structure 79. On either side of this central region are two identical vertical structures. Each structure consists of a base layer 74, a middle layer 75, and a top layer 91. A vertical channel 81 is formed within each of these structures. The top of the device is covered by a layer 86, which has circular features 88, 89 and 92. A layer 80 is also indicated on the right side of the device. The entire device is labeled 70.

FIG. 2